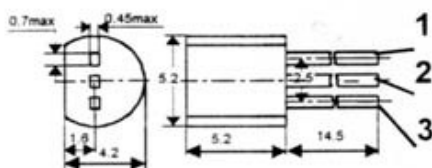


ML 406

Silicon controlled rectifier (SCR)
in TO-92 package



Pinouts:

1- Anode, 2- Gate, 3- Cathode

Maximum ratings

Symbol	Parameter, units	Limits
V_{drm}	Peak repetitive forward voltage, V, $R_{gk} = 1k\Omega$	400
V_{rrm}	Repetitive peak reverse voltage, V	6
$I_{t(rms)}$	On-state current, A, All Conduction Angles	0.8
$I_t(A_V)$	Average on-state current, A, Half Cycle, $\theta = 180^\circ$	0.5
$I_{t(sm)}$	Nonrepetition on-state current, A, Half Cycle, 50Hz	7.0
V_{grm}	Peak reverse gate voltage, V, $I_g = 0.01mA$	6.0

Electrical characteristics ($T_A = 25^\circ C$)

Symbol	Parameter, units test conditions	Limits	
		min	max
I_{drm}	Off state leakage current, μA , @ V_{drm} , $R_{gk} = 1k\Omega$		1
V_t	On state voltage, V, $I_t = 1.2A$		1.93
I_{gt}	Gate trigger current, mA, $V_d = 6V$		0.12
V_{gt}	Gate trigger voltage, V, $V_d = 6V$		0.8
I_h	Holding current, mA, $R_{gk} = 1k\Omega$		5
dV/dt	Crit. rate of voltage rise, V/ μs , $V_d = 0.67V_{drm}$, $R_{gk} = 1k\Omega$	25	
dI/dt	Crit. rate of current rise, A/ μs , $I_g = 10mA$, $dI_g/dt = 0.1A/\mu s$	30	
t_{gd}	Gate control delay time, ns, $I_g = 10mA$, $dI_g/dt = 0.1A/\mu s$		200